

查询FRM5N141GW供应商
**InGaAs-APD/Preamp
Receiver**

捷多邦, 专业PCB打样工厂, 24小时加急出货

FRM5N141GW

FEATURES

- Small Form Factor Package(GW): 9 pins coplanar
- Integrated Design Optimizes Performance at Bit Rates up to 12.5Gb/s
- High Sensitivity: -27dBm (typ.)
- Electrical Differential Output
- Wide Bandwidth: 10.5GHz (typ.)
- Operates in both C and L wavelength bands



APPLICATIONS

This APD with HBT preamplifier is intended to function as an optical receiver at 1,310nm or 1,530-1,610nm in SONET, SDH, DWDM or other optical fiber systems operating up to 12.5Gb/s. The typical transimpedance (Z_t) value of $1,300\Omega$ optimizes the total bandwidth for 10Gb/s application. The detector preamplifier is DC coupled and has an electrical differential output.

DESCRIPTION

The FRM5N141GW incorporates a high bandwidth InGaAs APD photo diode, a GaAs HBT IC amplifier in a hermetically sealed Small Form Factor package (SFF). The APD is processed with modern MOVPE techniques resulting in a reliable performance over a wide range of operating conditions. The lens coupling system and the single mode fiber are assembled using Nd YAG welding.

ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Storage Temperature	T_{stg}	-40 to +85	$^\circ\text{C}$
Operating Temperature	T_{op}	-5 to +75	$^\circ\text{C}$
Supply Voltage	V_{ss}	-6 to 0	V
PIN Reverse Voltage	V_R	0 to V_B (Note)	V
PIN Reverse Current	$I_{R(peak)}$	3	mA

Note: Since V_B may vary from device-to-device, V_B data is attached to each device for reference.

OPTICAL & ELECTRICAL CHARACTERISTICS

(T_C=25°C, λ=1,550nm, V_{SS}=-5.2V, unless otherwise specified)

Parameter	Symbol	Test Conditions	Limits			Unit	
			Min.	Typ.	Max.		
APD Responsivity	R13	λ = 1,310nm, M=1	0.75	0.85	-	A/W	
	R15	λ = 1,550nm, M=1	0.75	0.90	-		
	R16	λ = 1,610nm, M=1	-	0.80	-		
APD Breakdown Voltage	VB	ID = 10μA	20.0	25.0	30.0	V	
Temperature Coefficient of VB	γ	Note (1)	0.03	0.05	0.07	V/°C	
AC Transimpedance	Z _t	f = 750MHz, Single-end	900	1300	-	Ω	
Output Common Voltage	V _{out}	-	-	-400	-	mV	
Maximum Output Voltage Swing	V _{clip}	Saturated Output Voltage	400	600	800	mV	
Bandwidth	BW	-3dB from 750MHz, Pin=-20dBm	M=9	8.5	10.5	-	GHz
			M=3	8.5	10.5	-	
Lower Cut-off Frequency	f _{cl}	-3dB from 750MHz, Pin=-20dBm	-	40	100	kHz	
Peaking	d _{pk}	130MHz to BW, Pin=-20dBm, M=9	-	0.5	1.5	dB	
Group Delay Deviation	GD	1GHz to 6GHz, Pin=-20dBm, M=9	-	15	40	ps _{p-p}	
		1GHz to 8GHz, Pin=-20dBm, M=9	-	30	60		
Output Return Loss	S ₂₂	130MHz to 6GHz	-	12	-	dB	
		130MHz to 8GHz	-	10	-		
Minimum Sensitivity	P _r	10Gb/s, NRZ, PRBS=2 ³¹ -1, B.E.R.=10 ⁻¹² , VR=Optimum	25°C, R _{ext} =13dB	-	-27.0	-25.0	dBm
			25°C, R _{ext} =10dB	-	-26.0	-	
			25°C, R _{ext} =8.2dB	-	-25.0	-	
			70°C, R _{ext} =13dB	-	-26.0	-24.0	
Maximum Overload	P _o	10Gb/s, NRZ, PRBS=2 ³¹ -1, B.E.R.=10 ⁻¹² , M=3	R _{ext} =13dB	-7	-5	-	dBm
			R _{ext} =10dB	-	-4.5	-	
			R _{ext} =8.2dB	-	-4.0	-	
Optical Return Loss	ORL	λ = 1,550nm	27	-	-	dB	
		λ = 1,310nm	27	-	-		
Power Supply Current	I _{SS}	-	-	110	130	mA	
Power Supply Voltage	V _{SS}	-	-5.46	-5.20	-4.94	V	
Thermistor Resistance	R _{th}	-	9.5	10.0	10.5	kΩ	
Thermistor B Constant	B	-	3800	3900	4000	K	

Note 1: γ=ΔVB/dT_C

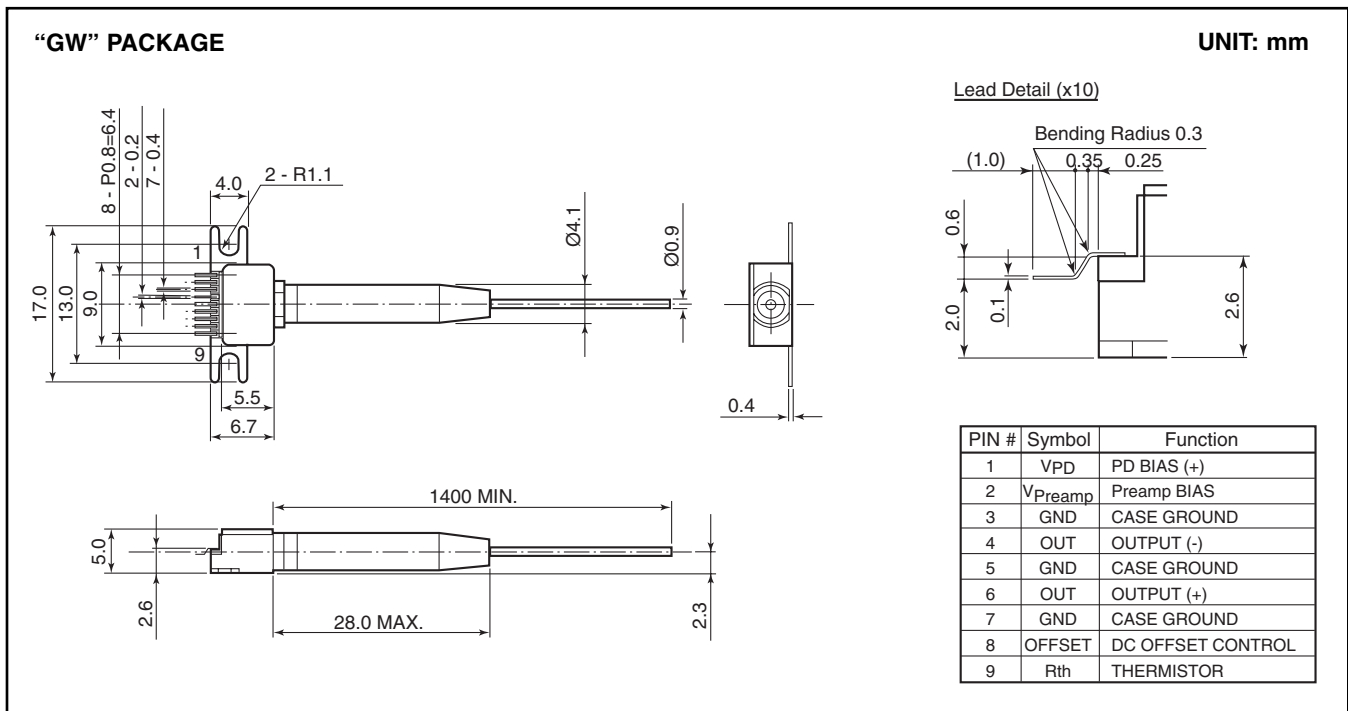
Note: All the parameters are measured with 50Ω, DC-coupled and 0V output offset.

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Notes

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- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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